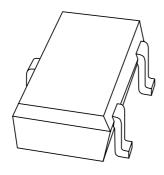
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **1PS300** High-speed double diode

Product data sheet Supersedes data of 1996 Oct 04 1999 May 26



# **High-speed double diode**

1PS300

### **FEATURES**

- Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 80 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

# **APPLICATIONS**

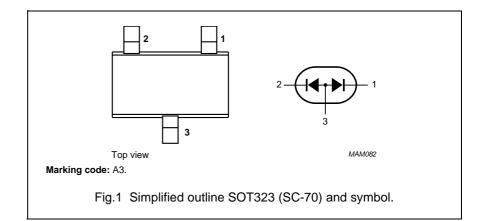
 High-speed switching in e.g. surface mounted circuits.

### **DESCRIPTION**

The 1PS300 consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in the very small rectangular SOT323 (SC-70) plastic SMD package.

### **PINNING**

PIN	DESCRIPTION	
1	cathode (k1)	
2	cathode (k2)	
3	common anode	



# **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per diode	Per diode						
V <sub>RRM</sub>	repetitive peak reverse voltage		_	85	V		
V <sub>R</sub>	continuous reverse voltage		_	80	V		
I <sub>F</sub>	continuous forward current	single diode loaded; see Fig.2; note 1	_	200	mA		
		double diode loaded; see Fig.2; note 1	_	170	mA		
I <sub>FRM</sub>	repetitive peak forward current		_	500	mA		
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge					
		t = 1 μs	_	4	Α		
		t = 1 s	_	0.5	Α		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	300	mW		
T <sub>stg</sub>	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		

### Note

1. Device mounted on an FR4 printed-circuit board.

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# High-speed double diode

1PS300

# **ELECTRICAL CHARACTERISTICS**

 $T_{i}$  = 25  $^{\circ}C$  unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		TYP.	MAX.	UNIT		
Per diode	Per diode						
V <sub>F</sub>	forward voltage	see Fig.3					
		I <sub>F</sub> = 1 mA	610	_	mV		
		I <sub>F</sub> = 10 mA	740	_	mV		
		I <sub>F</sub> = 50 mA	_	1	V		
		I <sub>F</sub> = 100 mA	_	1.2	V		
I <sub>R</sub>	reverse current	see Fig.4					
		V <sub>R</sub> = 25 V	_	30	nA		
		V <sub>R</sub> = 80 V	_	0.5	μΑ		
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	_	30	μΑ		
		V <sub>R</sub> = 80 V; T <sub>j</sub> = 150 °C	_	100	μΑ		
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.5	_	2	pF		
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.6	_	4	ns		
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.7	_	1.75	V		

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		200	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	415	K/W

# Note

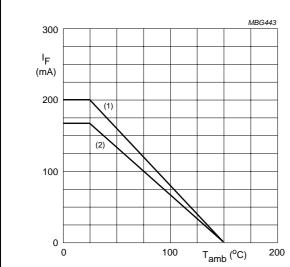
1. Device mounted on an FR4 printed-circuit board.

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# High-speed double diode

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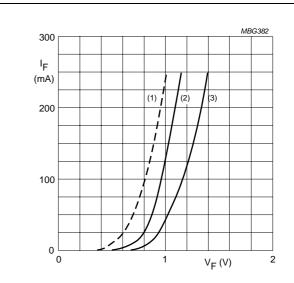
### **GRAPHICAL DATA**



Device mounted on an FR4 printed-circuit board.

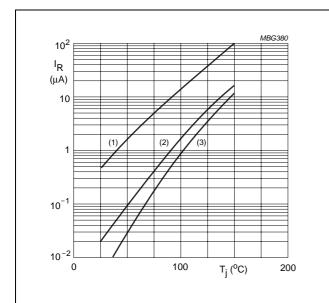
- (1) Single diode loaded.
- (2) Double diode loaded.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



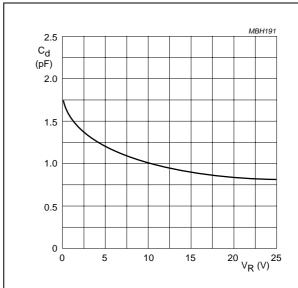
- (1)  $T_i = 150 \,^{\circ}\text{C}$ ; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



- (1)  $V_R = 80 \text{ V}$ ; maximum values.
- (2)  $V_R = 80 \text{ V}$ ; typical values.
- (3)  $V_R = 25 \text{ V}$ ; typical values.

Fig.4 Reverse current as a function of junction temperature.



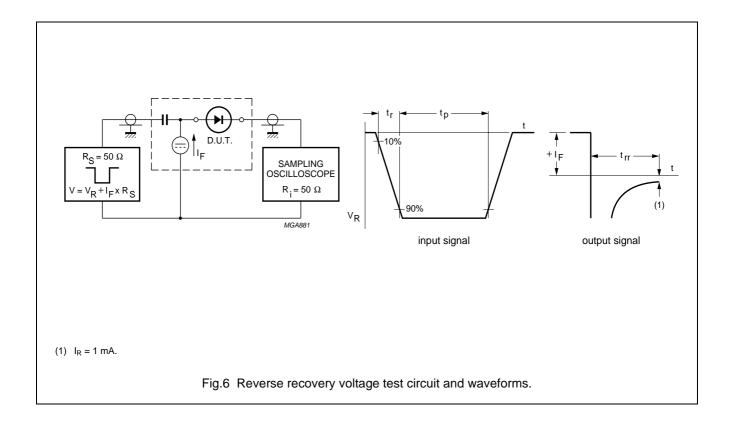
f = 1 MHz;  $T_j = 25 \,^{\circ}\text{C}$ .

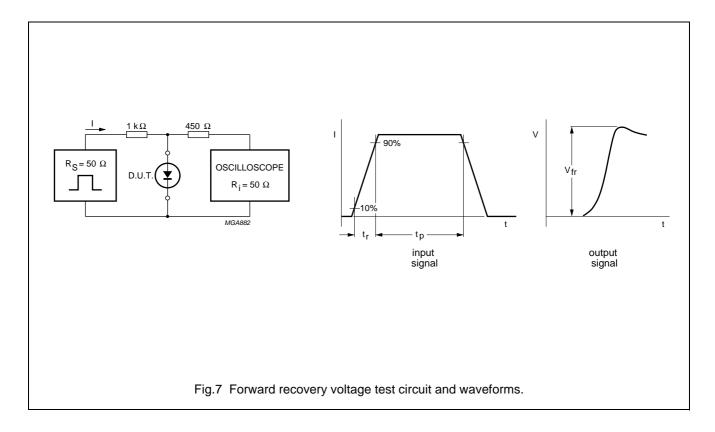
Fig.5 Diode capacitance as a function of reverse voltage; typical values.

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# High-speed double diode

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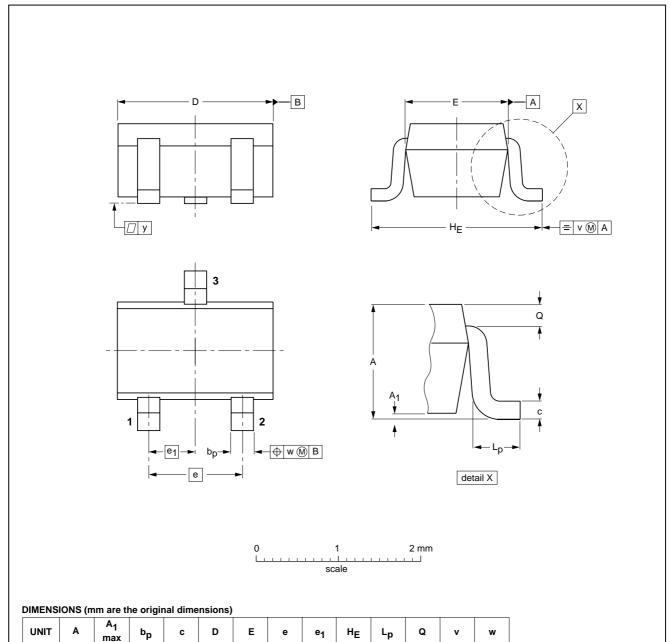
# High-speed double diode

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# **PACKAGE OUTLINE**

# Plastic surface mounted package; 3 leads

**SOT323** 



οι	JTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VE	RSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DATE	
S	OT323			SC-70		$\bigoplus \bigoplus$	97-02-28

0.65

0.45 0.15 0.23 0.13

0.2

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0.4 0.3

0.1

1.1

mm

0.25 0.10 2.2 1.8 1.35 1.15

# High-speed double diode

1PS300

### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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